



# STP13N95K3, STF13N95K3 STW13N95K3

N-channel 950 V, 0.68  $\Omega$ , 10 A, TO-220, TO-220FP, TO-247  
SuperMESH3™ Power MOSFET

Preliminary data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>	P <sub>w</sub>
STP13N95K3	950 V	< 0.85 $\Omega$	10 A	190 W
STF13N95K3	950 V	< 0.85 $\Omega$	10 A	40 W
STW13N95K3	950 V	< 0.85 $\Omega$	10 A	190 W

- 100% avalanche tested
- Extremely large avalanche performance
- Gate charge minimized
- Very low intrinsic capacitances
- Zener-protected

## Application

- Switching applications

## Description

The new SuperMESH3™ series of Power MOSFETS is the result of the fine-tuning of ST's well-established strip-based PowerMESH™ layout with a new optimized vertical structure. The innovative design offer significantly reduced on-resistance, exceptional dynamic performance and very large avalanche capability, making the device suitable for the most demanding applications.

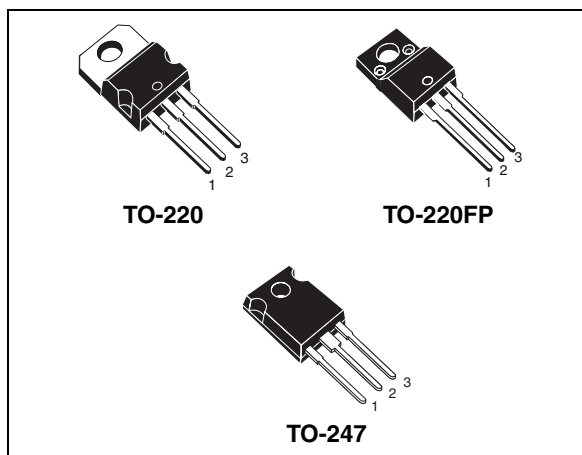


Figure 1. Internal schematic diagram

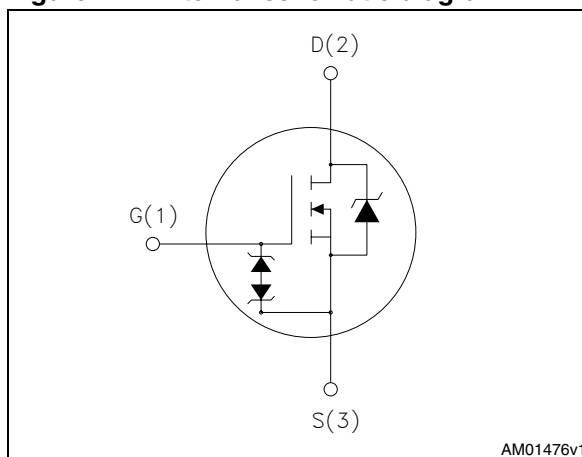


Table 1. Device summary

Order code	Marking	Package	Packaging
STF13N95K3	13N95K3	TO-220FP	Tube
STP13N95K3	13N95K3	TO-220	Tube
STW13N95K3	13N95K3	TO-247	Tube

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$V_{GS}$	Gate- source voltage	30			V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	10	10 <sup>(1)</sup>	10	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	6.3	6.3 <sup>(1)</sup>	6.3	A
$I_{DM}$ <sup>(2)</sup>	Drain current (pulsed)	40	40 <sup>(1)</sup>	40	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	190	40	190	W
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ max)	13			A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	TBD			mJ
$dv/dt$ <sup>(3)</sup>	Peak diode recovery voltage slope	6			V/ns
$V_{ISO}$	Insulation withstand voltage (AC)		2500		
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150			°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 10\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ , peak  $V_{DS} \leq V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.66	3.13	0.66	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.50		50.00	°C/W
$T_J$	Maximum lead temperature for soldering purpose	300			°C/W

## 2 Electrical characteristics

(T<sub>case</sub> = 25°C unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	950			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max rating V <sub>DS</sub> = Max rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V; V <sub>DS</sub> = 0			10	μA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 100 μA	3	4	5	V
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A		0.68	0.85	Ω

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 13 A	-	TBD	-	S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	V <sub>DS</sub> = 100 V, f = 1 MHz, V <sub>GS</sub> = 0	-	1700 178 2	-	pF pF pF
C <sub>o(tr)</sub> <sup>(2)</sup>	Equivalent capacitance time related	V <sub>DS</sub> = 0 to 760 V, V <sub>GS</sub> = 0	-	TBD	-	pF
C <sub>o(er)</sub> <sup>(3)</sup>	Equivalent capacitance energy related	V <sub>DS</sub> = 0 to 760 V, V <sub>GS</sub> = 0	-	TBD	-	pF
R <sub>g</sub>	Gate input resistance	f = 1 MHz open drain	-	2	-	Ω
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	V <sub>DD</sub> = 760 V, I <sub>D</sub> = 10 A, V <sub>GS</sub> = 10 V (see Figure 3)	-	49 TBD TBD	-	nC nC nC

1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5%
2. C<sub>oss eq.</sub> time related is defined as a constant equivalent capacitance giving the same charging time as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>
3. C<sub>oss eq.</sub> energy related is defined as a constant equivalent capacitance giving the same stored energy as C<sub>oss</sub> when V<sub>DS</sub> increases from 0 to 80% V<sub>DSS</sub>

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 475 \text{ V}$ , $I_D = 5 \text{ A}$ , $R_G = 4.7 \Omega$ , $V_{GS} = 10 \text{ V}$ (see Figure 2)	-	TBD	-	ns
$t_r$	Rise time			TBD		ns
$t_{d(off)}$	Turn-off-delay time			TBD		ns
$t_f$	Fall time			TBD		ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		10	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				40	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 10 \text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 10 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ (see Figure 4)	-	TBD		ns
$Q_{rr}$	Reverse recovery charge			TBD		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			TBD		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 10 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 60 \text{ V}$ $T_J = 150 \text{ }^\circ\text{C}$ (see Figure 4)	-	TBD		ns
$Q_{rr}$	Reverse recovery charge			TBD		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			TBD		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 8. Gate-source Zener diode**

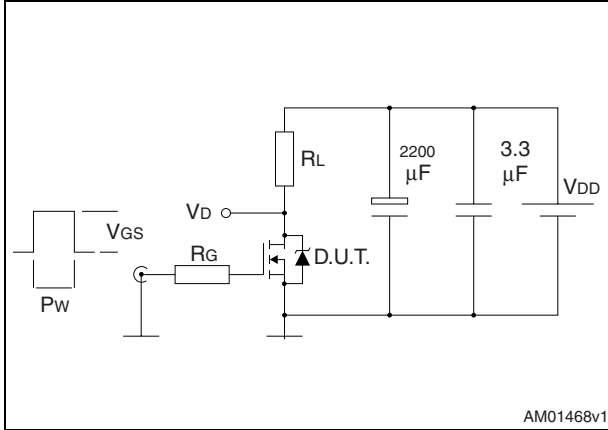
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{gs} = \pm 1 \text{ mA}$ (open drain)	-30	-	30	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Test circuits

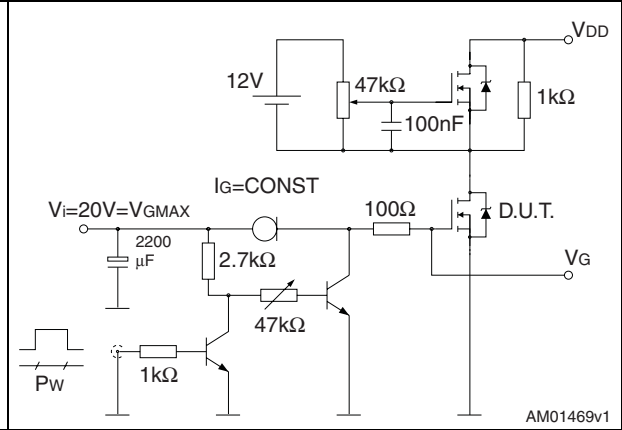
### 3 Test circuits

**Figure 2. Switching times test circuit for resistive load**



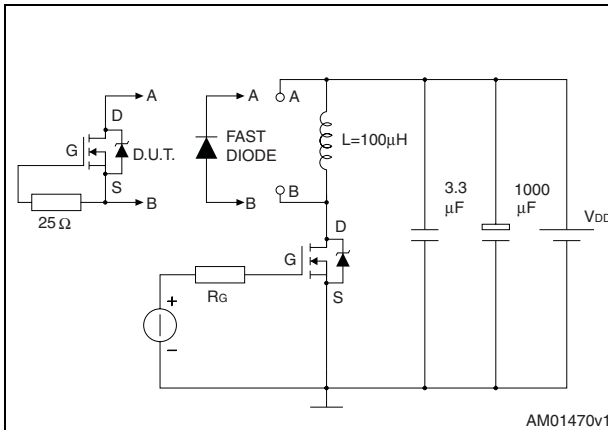
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**Figure 3. Gate charge test circuit**



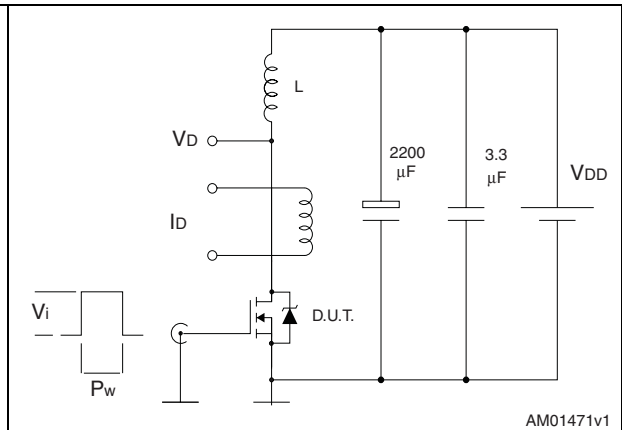
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**Figure 4. Test circuit for inductive load switching and diode recovery times**



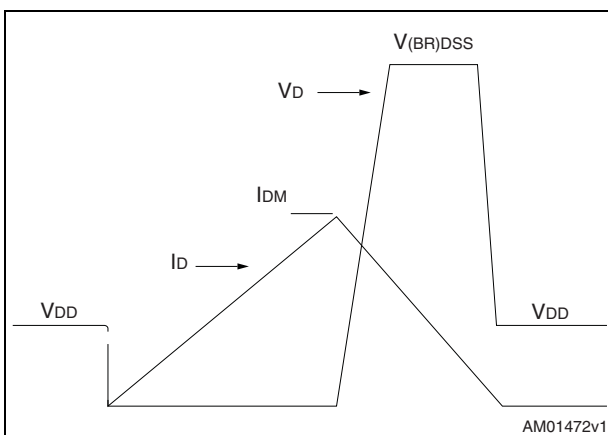
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**Figure 5. Unclamped inductive load test circuit**



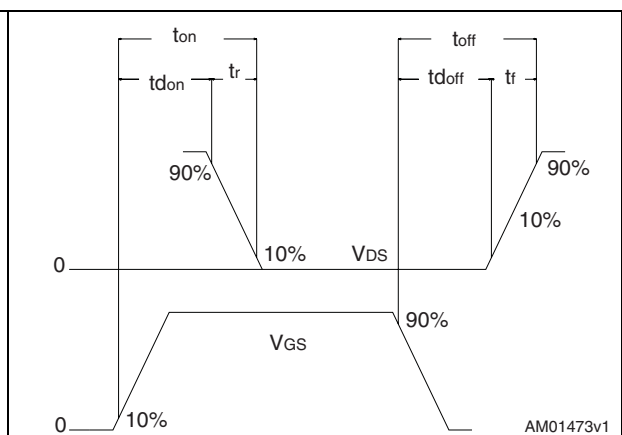
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**Figure 6. Unclamped inductive waveform**



AM01472v1

**Figure 7. Switching time waveform**



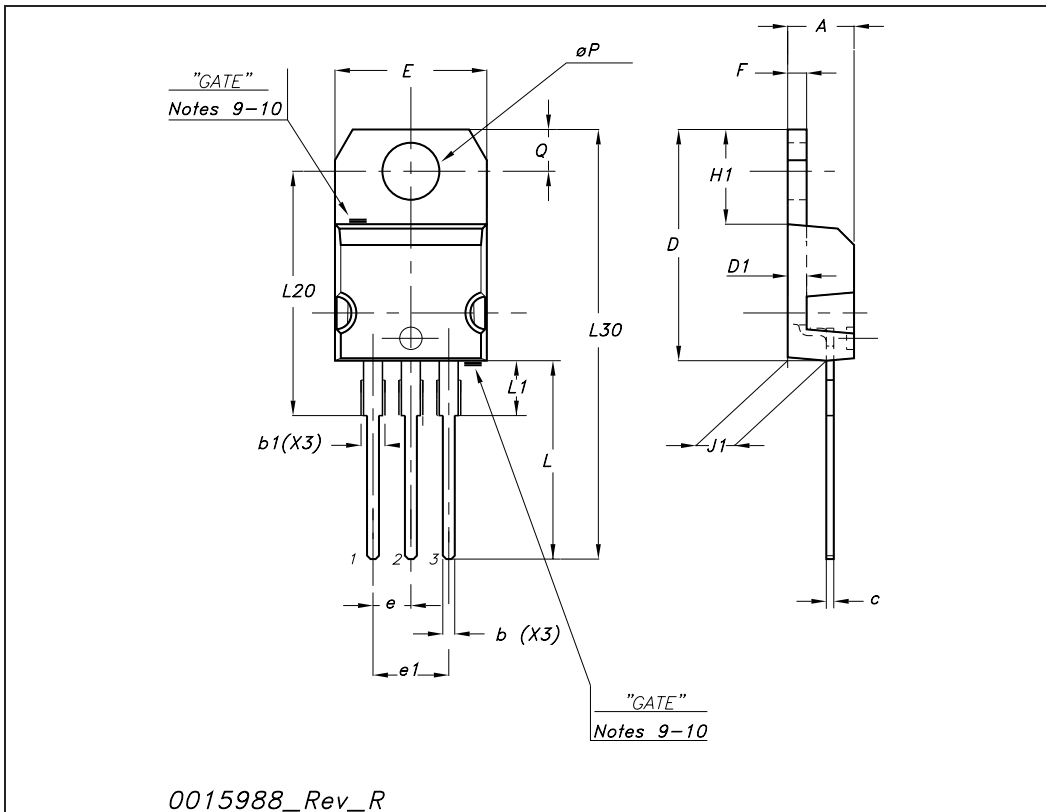
AM01473v1

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

TO-220 mechanical data

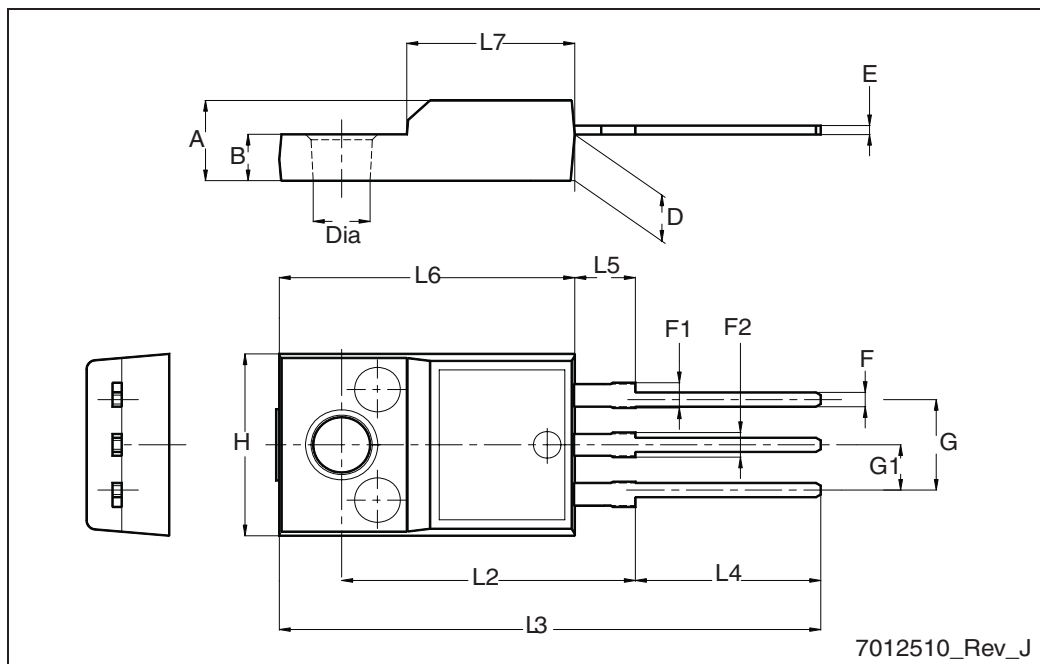
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116





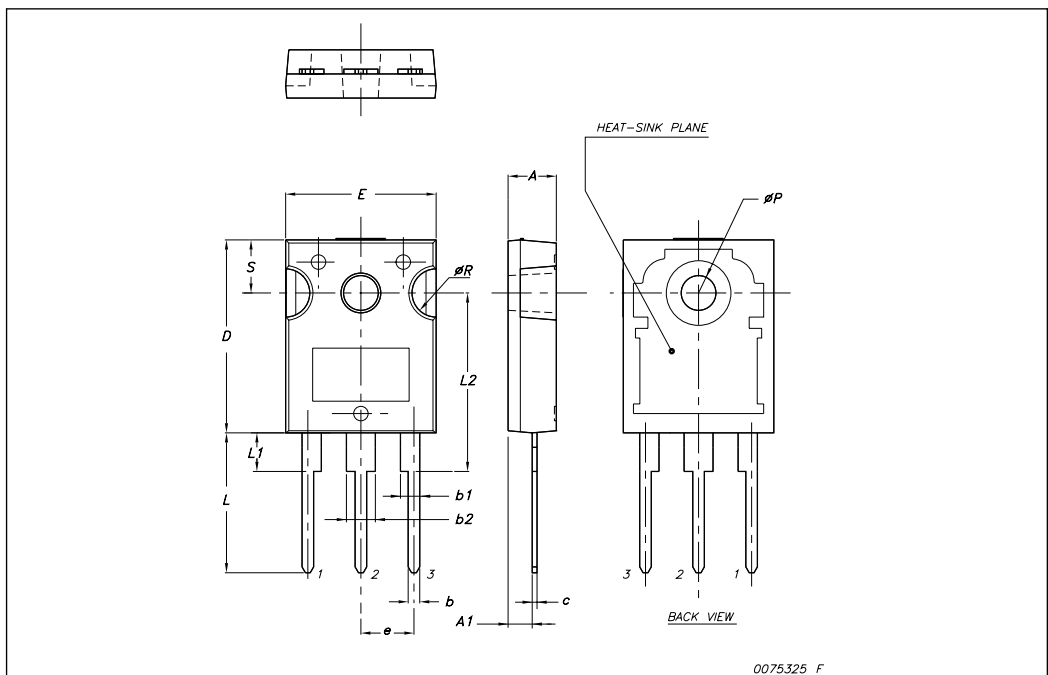
TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



## TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
$\varnothing P$	3.55		3.65
$\varnothing R$	4.50		5.50
S		5.50	



## 5 Revision history

Table 9. Document revision history

Date	Revision	Changes
15-May-2009	1	First release

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